

Substitute for form 1449A/PTO  
**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**  
(Use as many sheets as necessary)

Complete if Known	
Application Number	Unknown
Filing Date	Even Date Herewith
First Named Inventor	Noble Jr., Wendell
Group Art Unit	Unknown
Examiner Name	Unknown

Sheet 1 of 1

Attorney Docket No: 303.257US4

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EXAMINER

*Quwe Hoang*

DATE CONSIDERED

*04/2004*